

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Isolated mounting base package
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

## 3. Applications

- Electronic thermostats (heating and cooling)
- · High power motor controls e.g. washing machines and vacuum cleaners

## 4. Quick reference data

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4; Fig. 5}$	-	-	100	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 59$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	12	A
Static chara	acteristics	· · · ·				
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	-	10	mA
		$V_D = 12 V; I_T = 0.1 A; T2+ G-;$ $T_j = 25 °C; Fig. 7$	-	-	10	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-;	-	-	10	mA
		T <sub>j</sub> = 25 °C; <u>Fig. 7</u>				

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2		sym051
3	G	gate		·
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

# 6. Ordering information

### Table 3.Ordering information

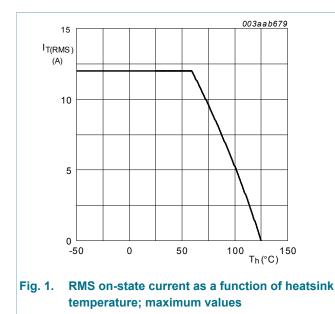
Type number	Package		
	Name	Description	Version
BTA312X-800E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

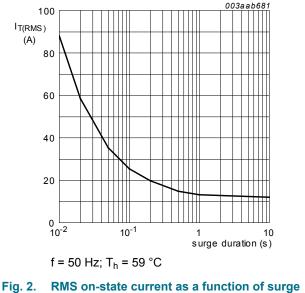
## 7. Limiting values

### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

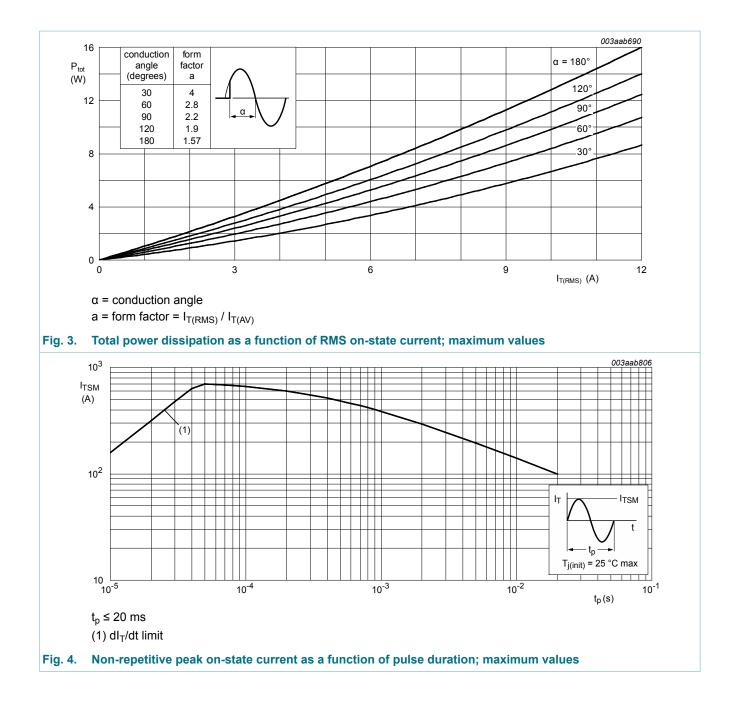
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 59$ °C; Fig. 1; Fig. 2; Fig. 3	-	12	A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{Fig. 4}; \text{Fig. 5}$	-	100	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 16.7 \text{ ms}$	-	110	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	50	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_{T}$ = 20 A; $I_{G}$ = 0.2 A; $dI_{G}/dt$ = 0.2 A/µs	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C





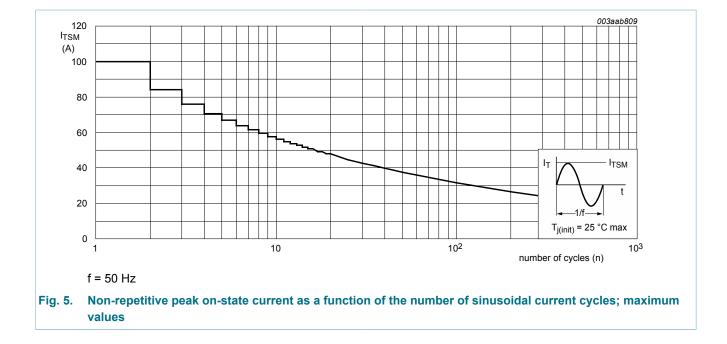
duration; maximum values

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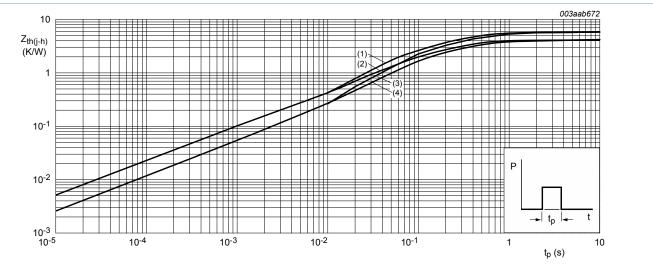
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## 8. Thermal characteristics

Table 5. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	full cycle or half cycle; with heatsink compound; Fig. 6	-	-	4	K/W
	heatsink	full cycle or half cycle; without heatsink compound; Fig. 6	-	-	5.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



(1) Unidirectional (half cycle) without heatsink compound

(2) Unidirectional (half cycle) with heatsink compound

(3) Bidirectional (full cycle) without heatsink compound

(4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

## 9. Isolation characteristics

Table 6. Iso	ation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>h</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

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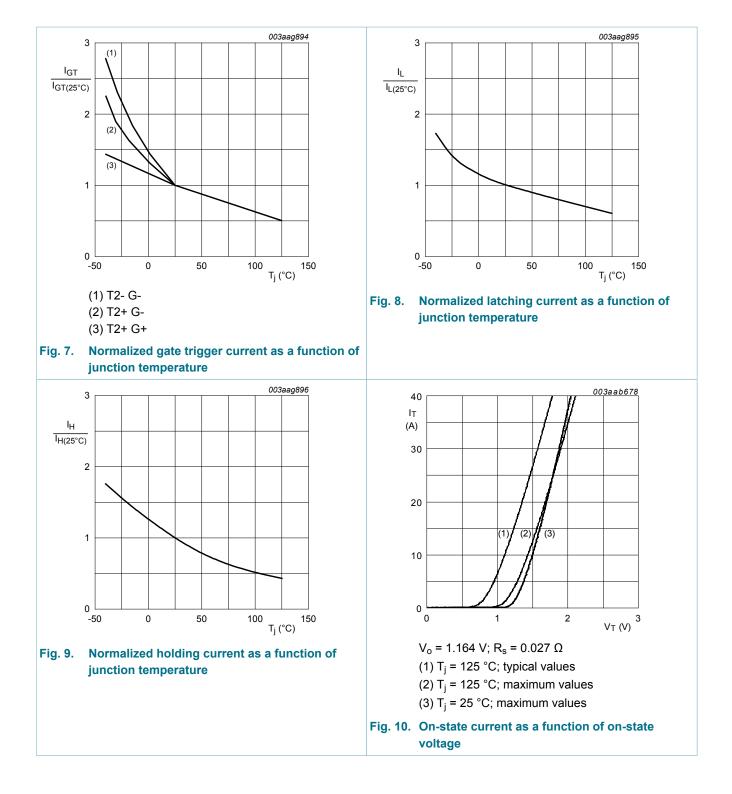
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# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	-	10	mA
IL	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	25	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	30	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	25	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics	· · · ·	1			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	50	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$\label{eq:VD} \begin{split} V_D &= 400 \text{ V};  \text{T}_{j} = 125 ^\circ\text{C};  \text{I}_{\text{T}(\text{RMS})} = 12 \text{ A}; \\ \text{d} V_{\text{com}}/\text{d} \text{t} &= 20  \text{V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit} \end{split}$	3	-	-	A/ms
		$V_D$ = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 12 A; dV <sub>com</sub> /dt = 10 V/µs; gate open circuit	6	-	-	A/ms
		$V_D$ = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 12 A; dV <sub>com</sub> /dt = 1 V/µs; gate open circuit	10	-	-	A/ms

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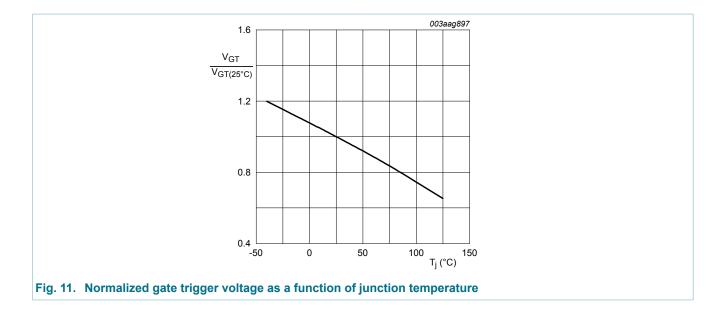


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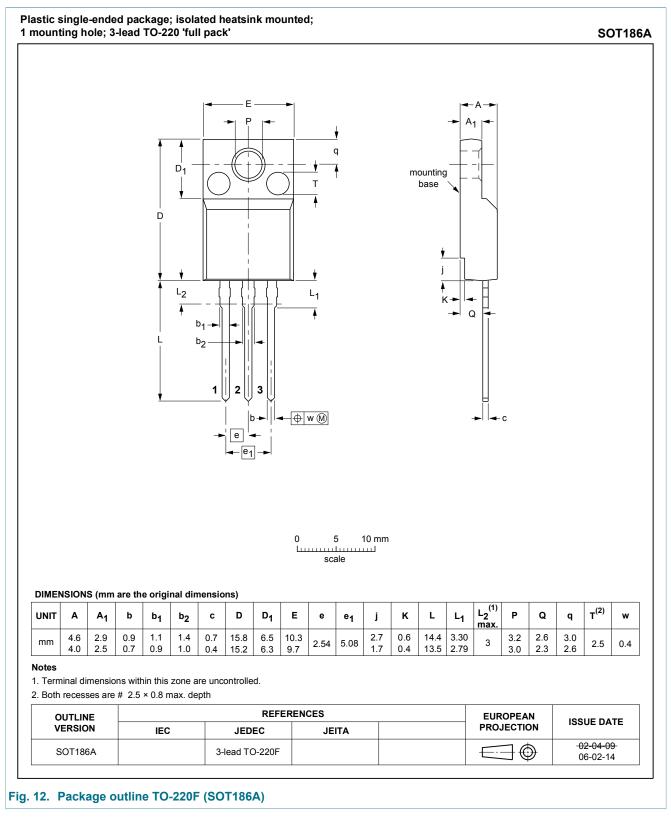
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### **3Q Hi-Com Triac**





## **11. Package outline**



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#### **3Q Hi-Com Triac**

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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